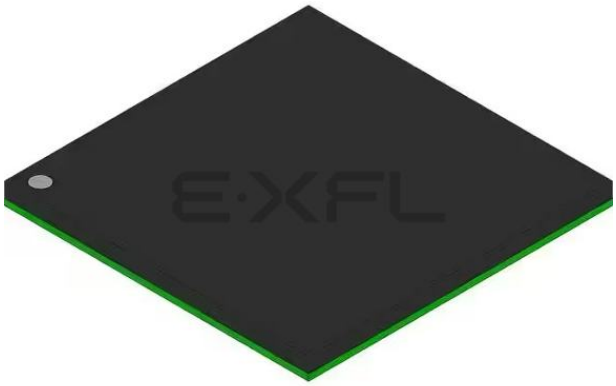

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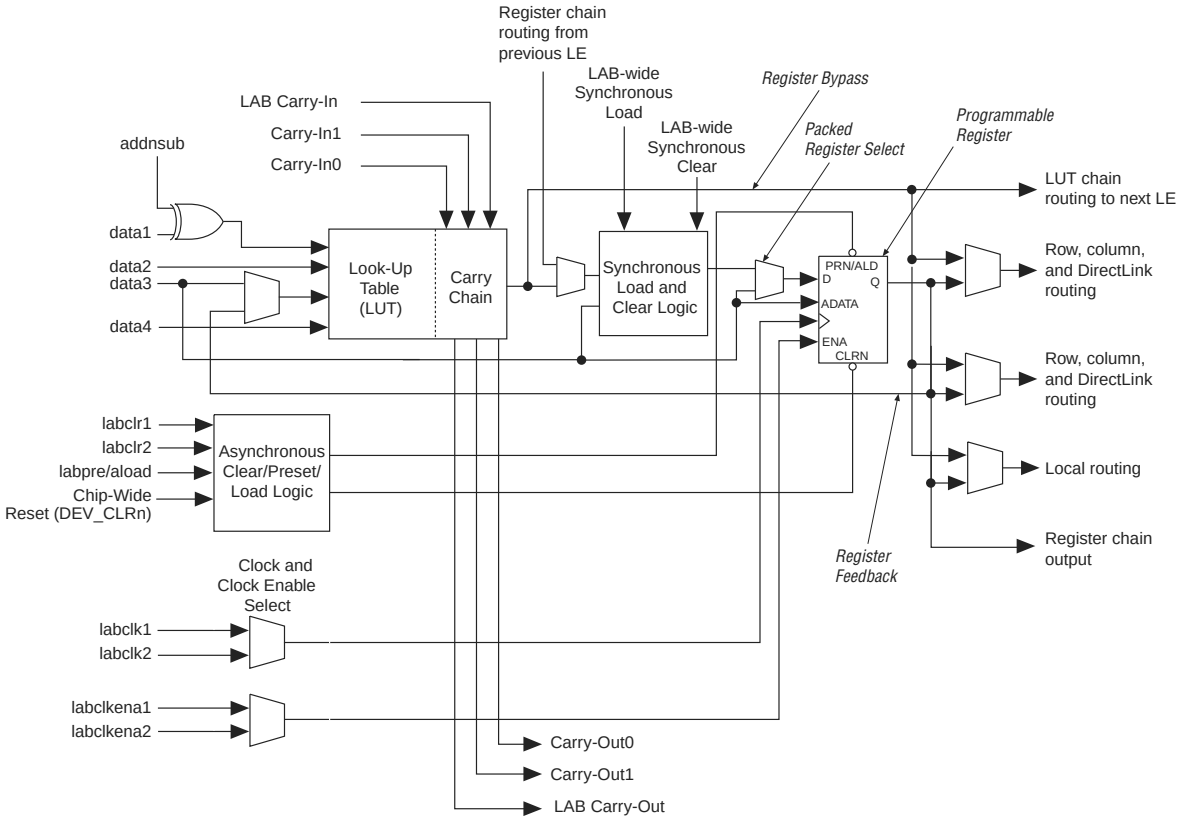
Understanding Embedded - CPLDs (Complex Programmable Logic Devices)

Embedded - CPLDs, or Complex Programmable Logic Devices, are highly versatile digital logic devices used in electronic systems. These programmable components are designed to perform complex logical operations and can be customized for specific applications. Unlike fixed-function ICs, CPLDs offer the flexibility to reprogram their configuration, making them an ideal choice for various embedded systems. They consist of a set of logic gates and programmable interconnects, allowing designers to implement complex logic circuits without needing custom hardware.

Applications of Embedded - CPLDs

Details	
Product Status	Active
Programmable Type	In System Programmable
Delay Time tpd(1) Max	9 ns
Voltage Supply - Internal	1.71V ~ 1.89V
Number of Logic Elements/Blocks	570
Number of Macrocells	440
Number of Gates	-
Number of I/O	160
Operating Temperature	-40°C ~ 100°C (TJ)
Mounting Type	Surface Mount
Package / Case	256-TFBGA
Supplier Device Package	256-MBGA (11x11)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=epm570zm256i8n

Figure 2–6. MAX II LE



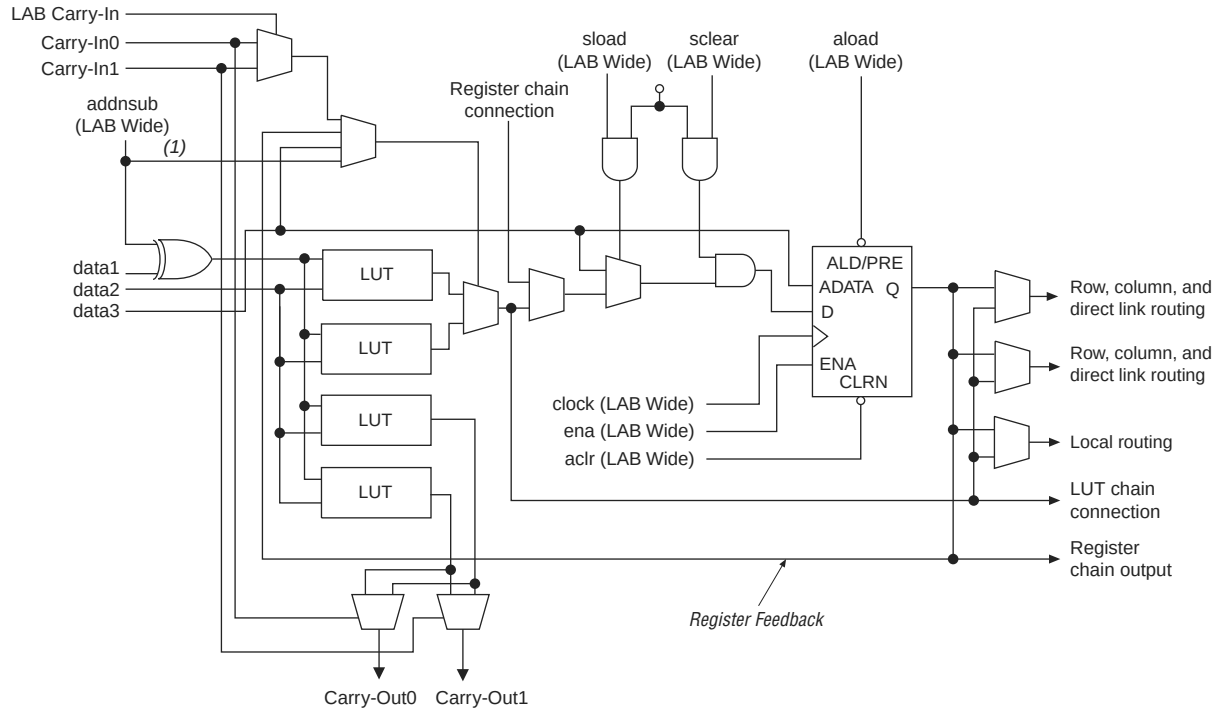
Each LE's programmable register can be configured for D, T, JK, or SR operation. Each register has data, true asynchronous load data, clock, clock enable, clear, and asynchronous load/preset inputs. Global signals, general-purpose I/O pins, or any LE can drive the register's clock and clear control signals. Either general-purpose I/O pins or LEs can drive the clock enable, preset, asynchronous load, and asynchronous data. The asynchronous load data input comes from the data3 input of the LE. For combinational functions, the LUT output bypasses the register and drives directly to the LE outputs.

Each LE has three outputs that drive the local, row, and column routing resources. The LUT or register output can drive these three outputs independently. Two LE outputs drive column or row and DirectLink routing connections and one drives local interconnect resources. This allows the LUT to drive one output while the register drives another output. This register packing feature improves device utilization because the device can use the register and the LUT for unrelated functions. Another special packing mode allows the register output to feed back into the LUT of the same LE so that the register is packed with its own fan-out LUT. This provides another mechanism for improved fitting. The LE can also drive out registered and unregistered versions of the LUT output.

The other two LUTs use the data1 and data2 signals to generate two possible carry-out signals: one for a carry of 1 and the other for a carry of 0. The `carry-in0` signal acts as the carry-select for the `carry-out0` output and `carry-in1` acts as the carry-select for the `carry-out1` output. LEs in arithmetic mode can drive out registered and unregistered versions of the LUT output.

The dynamic arithmetic mode also offers clock enable, counter enable, synchronous up/down control, synchronous clear, synchronous load, and dynamic adder/subtractor options. The LAB local interconnect data inputs generate the counter enable and synchronous up/down control signals. The synchronous clear and synchronous load options are LAB-wide signals that affect all registers in the LAB. The Quartus II software automatically places any registers that are not used by the counter into other LABs. The addnsub LAB-wide signal controls whether the LE acts as an adder or subtractor.

Figure 2–8. LE in Dynamic Arithmetic Mode



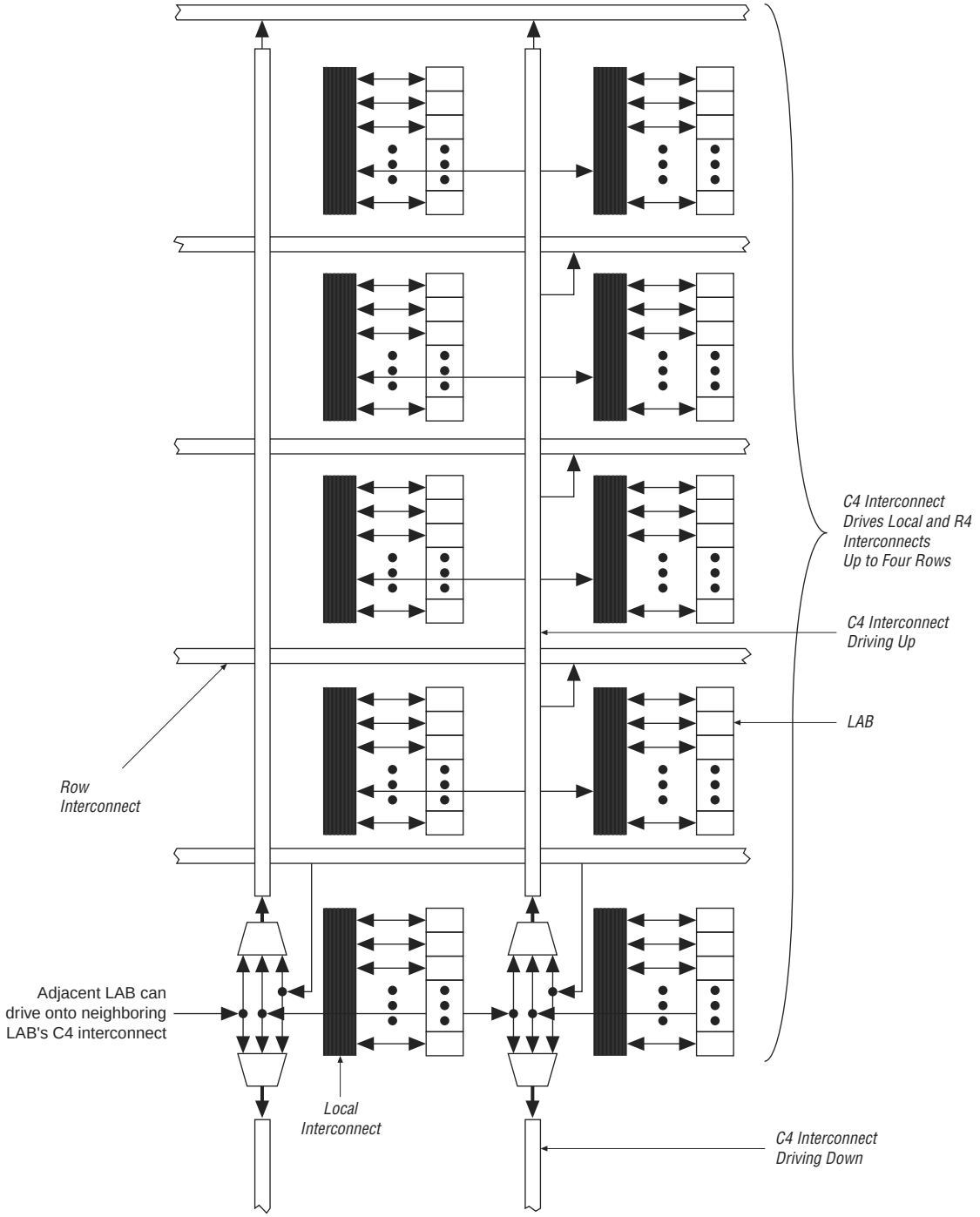
Note to Figure 2–8:

(1) The addnsub signal is tied to the carry input for the first LE of a carry chain only.

Carry-Select Chain

The carry-select chain provides a very fast carry-select function between LEs in dynamic arithmetic mode. The carry-select chain uses the redundant carry calculation to increase the speed of carry functions. The LE is configured to calculate outputs for a possible carry-in of 0 and carry-in of 1 in parallel. The `carry-in0` and `carry-in1` signals from a lower-order bit feed forward into the higher-order bit via the parallel carry chain and feed into both the LUT and the next portion of the carry chain. Carry-select chains can begin in any LE within an LAB.

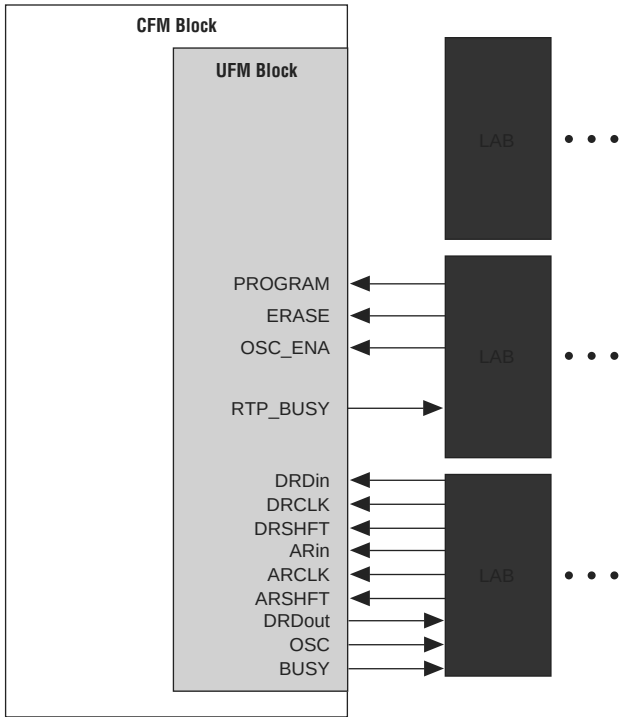
Figure 2–12. C4 Interconnect Connections *(Note 1)*



Note to Figure 2–12:

(1) Each C4 interconnect can drive either up or down four rows.

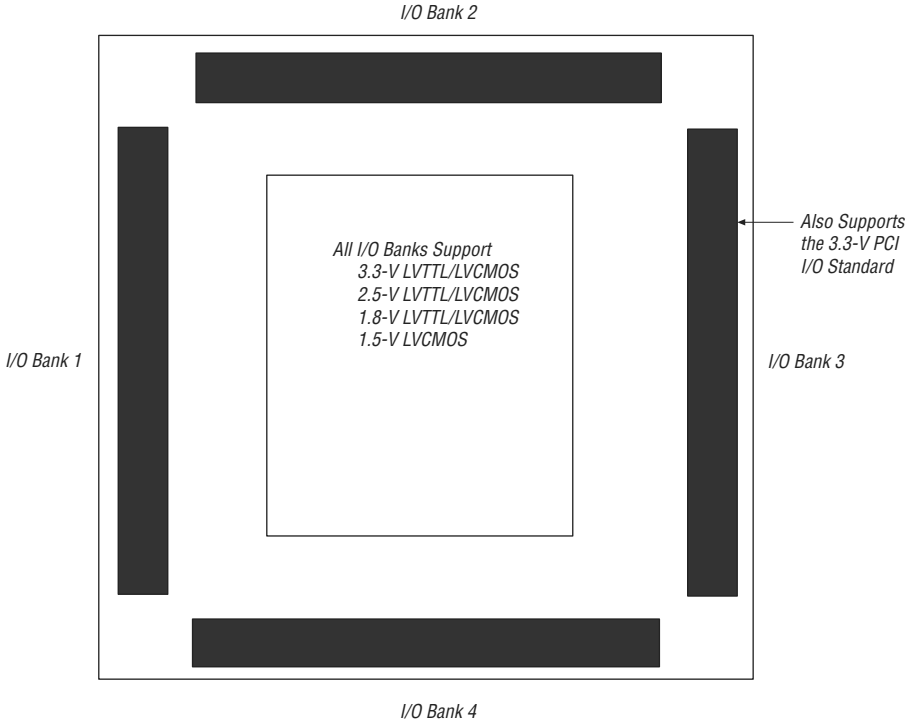
Figure 2–16. EPM240 UFM Block LAB Row Interface *(Note 1)*



Note to Figure 2–16:

(1) The UFM block inputs and outputs can drive to/from all types of interconnects, not only DirectLink interconnects from adjacent row LABs.

Figure 2–23. MAX II I/O Banks for EPM1270 and EPM2210 *(Note 1), (2)*



Notes to Figure 2–23:

(1) Figure 2–23 is a top view of the silicon die.

(2) Figure 2–23 is a graphical representation only. Refer to the pin list and the Quartus II software for exact pin locations.

Each I/O bank has dedicated V_{CCIO} pins that determine the voltage standard support in that bank. A single device can support 1.5-V, 1.8-V, 2.5-V, and 3.3-V interfaces; each individual bank can support a different standard. Each I/O bank can support multiple standards with the same V_{CCIO} for input and output pins. For example, when V_{CCIO} is 3.3 V, Bank 3 can support LVTTL, LVCMOS, and 3.3-V PCI. V_{CCIO} powers both the input and output buffers in MAX II devices.

The JTAG pins for MAX II devices are dedicated pins that cannot be used as regular I/O pins. The pins `TMS`, `TDI`, `TDO`, and `TCK` support all the I/O standards shown in Table 2–4 on page 2–27 except for PCI. These pins reside in Bank 1 for all MAX II devices and their I/O standard support is controlled by the V_{CCIO} setting for Bank 1.

PCI Compliance

The MAX II EPM1270 and EPM2210 devices are compliant with PCI applications as well as all 3.3-V electrical specifications in the *PCI Local Bus Specification Revision 2.2*. These devices are also large enough to support PCI intellectual property (IP) cores. Table 2–5 shows the MAX II device speed grades that meet the PCI timing specifications.

Table 2–6. Programmable Drive Strength *(Note 1)*

I/O Standard	IOH/IOL Current Strength Setting (mA)
3.3-V LVTTL	16
	8
3.3-V LVCMOS	8
	4
2.5-V LVTTL/LVCMOS	14
	7
1.8-V LVTTL/LVCMOS	6
	3
1.5-V LVCMOS	4
	2

Note to Table 2–6:

(1) The I_{OH} current strength numbers shown are for a condition of a $V_{OUT} = V_{OH}$ minimum, where the V_{OH} minimum is specified by the I/O standard. The I_{OL} current strength numbers shown are for a condition of a $V_{OUT} = V_{OL}$ maximum, where the V_{OL} maximum is specified by the I/O standard. For 2.5-V LVTTL/LVCMOS, the I_{OH} condition is V_{OUT} = 1.7 V and the I_{OL} condition is V_{OUT} = 0.7 V.

Slew-Rate Control

The output buffer for each MAX II device I/O pin has a programmable output slew-rate control that can be configured for low noise or high-speed performance. A faster slew rate provides high-speed transitions for high-performance systems. However, these fast transitions may introduce noise transients into the system. A slow slew rate reduces system noise, but adds a nominal output delay to rising and falling edges. The lower the voltage standard (for example, 1.8-V LVTTL) the larger the output delay when slow slew is enabled. Each I/O pin has an individual slew-rate control, allowing the designer to specify the slew rate on a pin-by-pin basis. The slew-rate control affects both the rising and falling edges.

Open-Drain Output

MAX II devices provide an optional open-drain (equivalent to open-collector) output for each I/O pin. This open-drain output enables the device to provide system-level control signals (for example, interrupt and write enable signals) that can be asserted by any of several devices. This output can also provide an additional wired-OR plane.

Programmable Ground Pins

Each unused I/O pin on MAX II devices can be used as an additional ground pin. This programmable ground feature does not require the use of the associated LEs in the device. In the Quartus II software, unused pins can be set as programmable GND on a global default basis or they can be individually assigned. Unused pins also have the option of being set as tri-stated input pins.

Bus Hold

Each MAX II device I/O pin provides an optional bus-hold feature. The bus-hold circuitry can hold the signal on an I/O pin at its last-driven state. Since the bus-hold feature holds the last-driven state of the pin until the next input signal is present, an external pull-up or pull-down resistor is not necessary to hold a signal level when the bus is tri-stated.

The bus-hold circuitry also pulls undriven pins away from the input threshold voltage where noise can cause unintended high-frequency switching. The designer can select this feature individually for each I/O pin. The bus-hold output will drive no higher than V_{CCIO} to prevent overdriving signals. If the bus-hold feature is enabled, the device cannot use the programmable pull-up option.

The bus-hold circuitry uses a resistor to pull the signal level to the last driven state. The *DC and Switching Characteristics* chapter in the *MAX II Device Handbook* gives the specific sustaining current for each V_{CCIO} voltage level driven through this resistor and overdrive current used to identify the next-driven input level.

The bus-hold circuitry is only active after the device has fully initialized. The bus-hold circuit captures the value on the pin present at the moment user mode is entered.

Programmable Pull-Up Resistor

Each MAX II device I/O pin provides an optional programmable pull-up resistor during user mode. If the designer enables this feature for an I/O pin, the pull-up resistor holds the output to the V_{CCIO} level of the output pin's bank.

☞ The programmable pull-up resistor feature should not be used at the same time as the bus-hold feature on a given I/O pin.

Programmable Input Delay

The MAX II IOE includes a programmable input delay that is activated to ensure zero hold times. A path where a pin directly drives a register, with minimal routing between the two, may require the delay to ensure zero hold time. However, a path where a pin drives a register through long routing or through combinational logic may not require the delay to achieve a zero hold time. The Quartus II software uses this delay to ensure zero hold times when needed.

MultiVolt I/O Interface

The MAX II architecture supports the MultiVolt I/O interface feature, which allows MAX II devices in all packages to interface with systems of different supply voltages. The devices have one set of VCC pins for internal operation (V_{CCINT}), and up to four sets for input buffers and I/O output driver buffers (V_{CCIO}), depending on the number of I/O banks available in the devices where each set of VCC pins powers one I/O bank. The EPM240 and EPM570 devices have two I/O banks respectively while the EPM1270 and EPM2210 devices have four I/O banks respectively.

Connect VCCIO pins to either a 1.5-V, 1.8 V, 2.5-V, or 3.3-V power supply, depending on the output requirements. The output levels are compatible with systems of the same voltage as the power supply (that is, when VCCIO pins are connected to a 1.5-V power supply, the output levels are compatible with 1.5-V systems). When VCCIO pins are connected to a 3.3-V power supply, the output high is 3.3 V and is compatible with 3.3-V or 5.0-V systems. Table 2–7 summarizes MAX II MultiVolt I/O support.

Table 2–7. MAX II MultiVolt I/O Support *(Note 1)*

	Input Signal					Output Signal				
VCCIO (V)	**1.5 V**	**1.8 V**	**2.5 V**	**3.3 V**	**5.0 V**	**1.5 V**	**1.8 V**	**2.5 V**	**3.3 V**	**5.0 V**
1.5	✓	✓	✓	✓	—	✓	—	—	—	—
1.8	✓	✓	✓	✓	—	✓ *(2)*	✓	—	—	—
2.5	—	—	✓	✓	—	✓ *(3)*	✓ *(3)*	✓	—	—
3.3	—	—	✓ *(4)*	✓	✓ *(5)*	✓ *(6)*	✓ *(6)*	✓ *(6)*	✓	✓ *(7)*

Notes to Table 2–7:

(1) To drive inputs higher than V_{CCIO} but less than 4.0 V including the overshoot, disable the I/O clamp diode. However, to drive 5.0-V inputs to the device, enable the I/O clamp diode to prevent V_I from rising above 4.0 V.

(2) When V_{CCIO} = 1.8 V, a MAX II device can drive a 1.5-V device with 1.8-V tolerant inputs.

(3) When V_{CCIO} = 2.5 V, a MAX II device can drive a 1.5-V or 1.8-V device with 2.5-V tolerant inputs.

(4) When V_{CCIO} = 3.3 V and a 2.5-V input signal feeds an input pin, the VCCIO supply current will be slightly larger than expected.

(5) MAX II devices can be 5.0-V tolerant with the use of an external resistor and the internal I/O clamp diode on the EPM1270 and EPM2210 devices.

(6) When V_{CCIO} = 3.3 V, a MAX II device can drive a 1.5-V, 1.8-V, or 2.5-V device with 3.3-V tolerant inputs.

(7) When V_{CCIO} = 3.3 V, a MAX II device can drive a device with 5.0-V TTL inputs but not 5.0-V CMOS inputs. In the case of 5.0-V CMOS, open-drain setting with internal I/O clamp diode (available only on EPM1270 and EPM2210 devices) and external resistor is required.

For information about output pin source and sink current guidelines, refer to the *AN 428: MAX II CPLD Design Guidelines*.

Referenced Documents

This chapter referenced the following documents:

- *AN 428: MAX II CPLD Design Guidelines*
- *DC and Switching Characteristics* chapter in the *MAX II Device Handbook*
- *Hot Socketing and Power-On Reset in MAX II Devices* chapter in the *MAX II Device Handbook*
- *Using User Flash Memory in MAX II Devices* chapter in the *MAX II Device Handbook*

Real-Time ISP

For systems that require more than DC logic level control of I/O pins, the real-time ISP feature allows you to update the CFM block with a new design image while the current design continues to operate in the SRAM logic array and I/O pins. A new programming file is updated into the MAX II device without halting the original design's operation, saving down-time costs for remote or field upgrades. The updated CFM block configures the new design into the SRAM upon the next power cycle. It is also possible to execute an immediate configuration of the SRAM without a power cycle by using a specific sequence of ISP commands. The configuration of SRAM without a power cycle takes a specific amount of time (t_{CONFIG}). During this time, the I/O pins are tri-stated and weakly pulled-up to V_{CCIO}.

Design Security

All MAX II devices contain a programmable security bit that controls access to the data programmed into the CFM block. When this bit is programmed, design programming information, stored in the CFM block, cannot be copied or retrieved. This feature provides a high level of design security because programmed data within flash memory cells is invisible. The security bit that controls this function, as well as all other programmed data, is reset only when the device is erased. The SRAM is also invisible and cannot be accessed regardless of the security bit setting. The UFM block data is not protected by the security bit and is accessible through JTAG or logic array connections.

Programming with External Hardware

MAX II devices can be programmed by downloading the information via in-circuit testers, embedded processors, the Altera® ByteblasterMV™, MasterBlaster™, ByteBlaster™ II, and USB-Blaster cables.

BP Microsystems, System General, and other programming hardware manufacturers provide programming support for Altera devices. Check their websites for device support information.

Referenced Documents

This chapter references the following documents:

- *DC and Switching Characteristics* chapter in the *MAX II Device Handbook*
- *IEEE 1149.1 (JTAG) Boundary-Scan Testing for MAX II Devices* chapter in the *MAX II Device Handbook*
- *Real-Time ISP and ISP Clamp for MAX II Devices* chapter in the *MAX II Device Handbook*
- *Using Jam STAPL for ISP via an Embedded Processor* chapter in the *MAX II Device Handbook*

4. Hot Socketing and Power-On Reset in MAX II Devices

MII51004-2.1

Introduction

MAX® II devices offer hot socketing, also known as hot plug-in or hot swap, and power sequencing support. Designers can insert or remove a MAX II board in a system during operation without undesirable effects to the system bus. The hot socketing feature removes some of the difficulties designers face when using components on printed circuit boards (PCBs) that contain a mixture of 3.3-, 2.5-, 1.8-, and 1.5-V devices.

The MAX II device hot socketing feature provides:

- Board or device insertion and removal
- Support for any power-up sequence
- Non-intrusive I/O buffers to system buses during hot insertion

This chapter contains the following sections:

MAX II Hot-Socketing Specifications

MAX II devices offer all three of the features required for the hot-socketing capability listed above without any external components or special design requirements. The following are hot-socketing specifications:

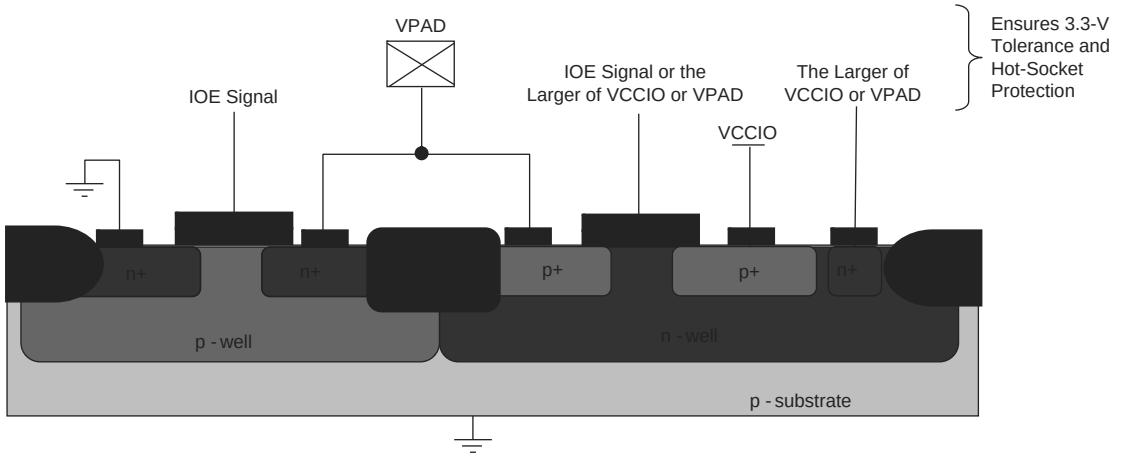
- The device can be driven before and during power-up or power-down without any damage to the device itself.
- I/O pins remain tri-stated during power-up. The device does not drive out before or during power-up, thereby affecting other buses in operation.
- Signal pins do not drive the V_{CCIO} or V_{CCINT} power supplies. External input signals to device I/O pins do not power the device V_{CCIO} or V_{CCINT} power supplies via internal paths. This is true if the V_{CCINT} and the V_{CCIO} supplies are held at GND.

☞ Altera uses `GND` as reference for the hot-socketing and I/O buffers circuitry designs. You must connect the `GND` between boards before connecting the V_{CCINT} and the V_{CCIO} power supplies to ensure device reliability and compliance to the hot-socketing specifications.

Devices Can Be Driven before Power-Up

Signals can be driven into the MAX II device I/O pins and `GCLK[3..0]` pins before or during power-up or power-down without damaging the device. MAX II devices support any power-up or power-down sequence (V_{CCIO1}, V_{CCIO2}, V_{CCIO3}, V_{CCIO4}, V_{CCINT}), simplifying the system-level design.

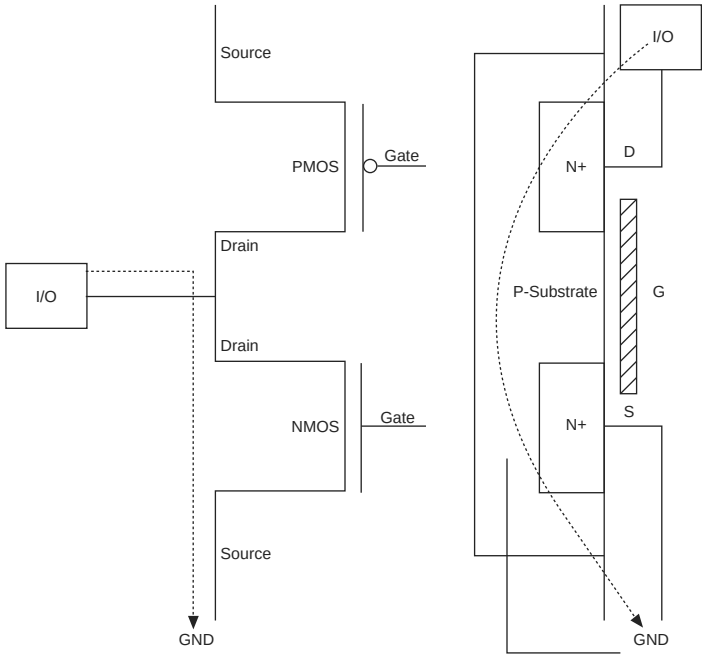
Figure 4–2. Transistor-Level Diagram of MAX II Device I/O Buffers



The CMOS output drivers in the I/O pins intrinsically provide electrostatic discharge (ESD) protection. There are two cases to consider for ESD voltage strikes: positive voltage zap and negative voltage zap.

A positive ESD voltage zap occurs when a positive voltage is present on an I/O pin due to an ESD charge event. This can cause the N+ (Drain)/ P-Substrate junction of the N-channel drain to break down and the N+ (Drain)/P-Substrate/N+ (Source) intrinsic bipolar transistor turn on to discharge ESD current from I/O pin to GND. The dashed line (see Figure 4–3) shows the ESD current discharge path during a positive ESD zap.

Figure 4–3. ESD Protection During Positive Voltage Zap



Recommended Operating Conditions

Table 5–2 shows the MAX II device family recommended operating conditions.

Table 5–2. MAX II Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCINT} *(1)*	3.3-V supply voltage for internal logic and ISP	MAX II devices	3.00	3.60	V
	2.5-V supply voltage for internal logic and ISP	MAX II devices	2.375	2.625	V
	1.8-V supply voltage for internal logic and ISP	MAX IIG and MAX IIZ devices	1.71	1.89	V
V_{CCIO} *(1)*	Supply voltage for I/O buffers, 3.3-V operation	—	3.00	3.60	V
	Supply voltage for I/O buffers, 2.5-V operation	—	2.375	2.625	V
	Supply voltage for I/O buffers, 1.8-V operation	—	1.71	1.89	V
	Supply voltage for I/O buffers, 1.5-V operation	—	1.425	1.575	V
V_I	Input voltage	*(2)*, *(3)*, *(4)*	–0.5	4.0	V
V_O	Output voltage	—	0	V_{CCIO}	V
T_J	Operating junction temperature	Commercial range	0	85	°C
		Industrial range	–40	100	°C
		Extended range *(5)*	–40	125	°C

Notes to Table 5–2:

(1) MAX II device in-system programming and/or user flash memory (UFM) programming via JTAG or logic array is not guaranteed outside the recommended operating conditions (for example, if brown-out occurs in the system during a potential write/program sequence to the UFM, users are recommended to read back UFM contents and verify against the intended write data).

(2) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V for input currents less than 100 mA and periods shorter than 20 ns.

(3) During transitions, the inputs may overshoot to the voltages shown in the following table based upon input duty cycle. The DC case is equivalent to 100% duty cycle. For more information about 5.0-V tolerance, refer to the *Using MAX II Devices in Multi-Voltage Systems* chapter in the *MAX II Device Handbook*.

V_{IN}	Max. Duty Cycle
4.0 V	100% (DC)
4.1	90%
4.2	50%
4.3	30%
4.4	17%
4.5	10%

(4) All pins, including clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.

(5) For the extended temperature range of 100 to 125° C, MAX II UFM programming (erase/write) is only supported via the JTAG interface. UFM programming via the logic array interface is not guaranteed in this range.

Table 5–6. 3.3-V LVCMOS Specifications (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{OH}	High-level output voltage	V_{CCIO} = 3.0, IOH = –0.1 mA *(1)*	V_{CCIO} – 0.2	—	V
V_{OL}	Low-level output voltage	V_{CCIO} = 3.0, IOL = 0.1 mA *(1)*	—	0.2	V

Table 5–7. 2.5-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	2.375	2.625	V
V_{IH}	High-level input voltage	—	1.7	4.0	V
V_{IL}	Low-level input voltage	—	–0.5	0.7	V
V_{OH}	High-level output voltage	IOH = –0.1 mA *(1)*	2.1	—	V
		IOH = –1 mA *(1)*	2.0	—	V
		IOH = –2 mA *(1)*	1.7	—	V
V_{OL}	Low-level output voltage	IOL = 0.1 mA *(1)*	—	0.2	V
		IOL = 1 mA *(1)*	—	0.4	V
		IOL = 2 mA *(1)*	—	0.7	V

Table 5–8. 1.8-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	1.71	1.89	V
V_{IH}	High-level input voltage	—	0.65 × V_{CCIO}	2.25 *(2)*	V
V_{IL}	Low-level input voltage	—	–0.3	0.35 × V_{CCIO}	V
V_{OH}	High-level output voltage	IOH = –2 mA *(1)*	V_{CCIO} – 0.45	—	V
V_{OL}	Low-level output voltage	IOL = 2 mA *(1)*	—	0.45	V

Table 5–9. 1.5-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	1.425	1.575	V
V_{IH}	High-level input voltage	—	0.65 × V_{CCIO}	V_{CCIO} + 0.3 *(2)*	V
V_{IL}	Low-level input voltage	—	–0.3	0.35 × V_{CCIO}	V
V_{OH}	High-level output voltage	IOH = –2 mA *(1)*	0.75 × V_{CCIO}	—	V
V_{OL}	Low-level output voltage	IOL = 2 mA *(1)*	—	0.25 × V_{CCIO}	V

Notes to Table 5–5 through Table 5–9:

(1) This specification is supported across all the programmable drive strength settings available for this I/O standard, as shown in the *MAX II Architecture* chapter (*I/O Structure section*) in the *MAX II Device Handbook*.

(2) This maximum V_{IH} reflects the JEDEC specification. The MAX II input buffer can tolerate a V_{IH} maximum of 4.0, as specified by the V_I parameter in Table 5–2.

Table 5–10. 3.3-V PCI Specifications *(Note 1)*

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	3.0	3.3	3.6	V
V_{IH}	High-level input voltage	—	0.5 × V_{CCIO}	—	V_{CCIO} + 0.5	V
V_{IL}	Low-level input voltage	—	–0.5	—	0.3 × V_{CCIO}	V
V_{OH}	High-level output voltage	IOH = –500 µA	0.9 × V_{CCIO}	—	—	V
V_{OL}	Low-level output voltage	IOL = 1.5 mA	—	—	0.1 × V_{CCIO}	V

Note to Table 5–10:

(1) 3.3-V PCI I/O standard is only supported in Bank 3 of the EPM1270 and EPM2210 devices.

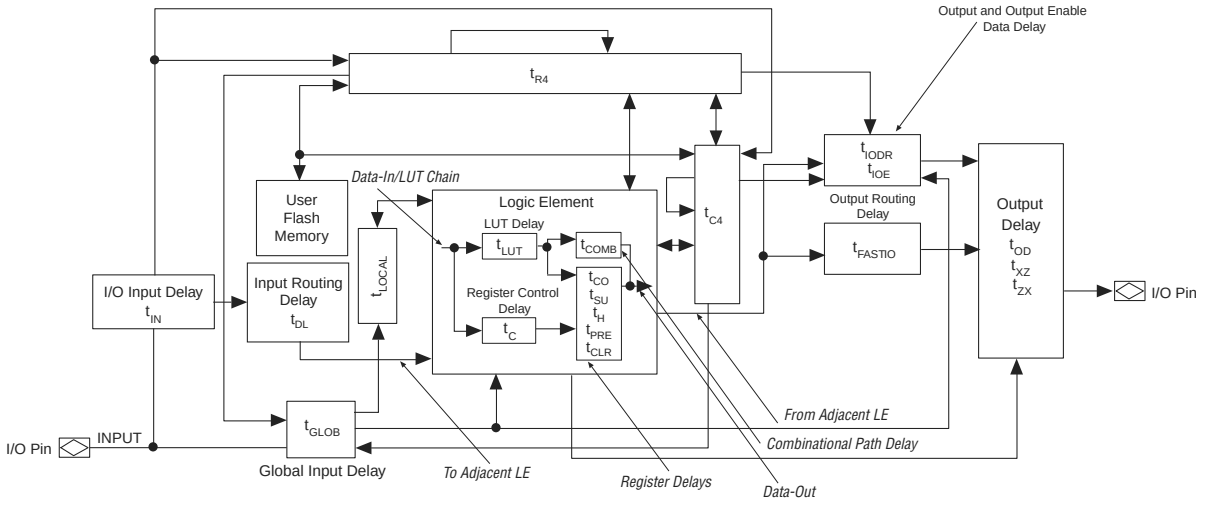
Bus Hold Specifications

Table 5–11 shows the MAX II device family bus hold specifications.

Table 5–11. Bus Hold Specifications

Parameter	Conditions	V_{CCIO} Level								Unit
		1.5 V		1.8 V		2.5 V		3.3 V		
		Min	Max	Min	Max	Min	Max	Min	Max	
Low sustaining current	V_{IN} > V_{IL} (maximum)	20	—	30	—	50	—	70	—	µA
High sustaining current	V_{IN} < V_{IH} (minimum)	–20	—	–30	—	–50	—	–70	—	µA
Low overdrive current	0 V < V_{IN} < V_{CCIO}	—	160	—	200	—	300	—	500	µA
High overdrive current	0 V < V_{IN} < V_{CCIO}	—	–160	—	–200	—	–300	—	–500	µA

Figure 5–2. MAX II Device Timing Model



The timing characteristics of any signal path can be derived from the timing model and parameters of a particular device. External timing parameters, which represent pin-to-pin timing delays, can be calculated as the sum of internal parameters.

Refer to the *Understanding Timing in MAX II Devices* chapter in the *MAX II Device Handbook* for more information.

This section describes and specifies the performance, internal, external, and UFM timing specifications. All specifications are representative of the worst-case supply voltage and junction temperature conditions.

Preliminary and Final Timing

Timing models can have either preliminary or final status. The Quartus II software issues an informational message during the design compilation if the timing models are preliminary. Table 5–13 shows the status of the MAX II device timing models.

Preliminary status means the timing model is subject to change. Initially, timing numbers are created using simulation results, process data, and other known parameters. These tests are used to make the preliminary numbers as close to the actual timing parameters as possible.

Final timing numbers are based on actual device operation and testing. These numbers reflect the actual performance of the device under the worst-case voltage and junction temperature conditions.

Table 5–13. MAX II Device Timing Model Status (Part 1 of 2)

Device	Preliminary	Final
EPM240	—	✓
EPM240Z *(1)*	—	✓
EPM570	—	✓
EPM570Z *(1)*	—	✓

Table 5–17. t_{ZX} IOE Microparameter Adders for Fast Slew Rate (Part 2 of 2)

Standard		MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
1.5-V LVCMOS	4 mA	—	1,118	—	1,454	—	1,789	—	580	—	588	—	588	ps
	2 mA	—	2,410	—	3,133	—	3,856	—	915	—	923	—	923	ps
3.3-V PCI	20 mA	—	19	—	25	—	31	—	72	—	71	—	74	ps

Table 5–18. t_{ZX} IOE Microparameter Adders for Slow Slew Rate

Standard		MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTL	16 mA	—	6,350	—	6,050	—	5,749	—	5,951	—	5,952	—	6,063	ps
	8 mA	—	9,383	—	9,083	—	8,782	—	6,534	—	6,533	—	6,662	ps
3.3-V LVCMOS	8 mA	—	6,350	—	6,050	—	5,749	—	5,951	—	5,952	—	6,063	ps
	4 mA	—	9,383	—	9,083	—	8,782	—	6,534	—	6,533	—	6,662	ps
2.5-V LVTTL / LVCMOS	14 mA	—	10,412	—	10,112	—	9,811	—	9,110	—	9,105	—	9,237	ps
	7 mA	—	13,613	—	13,313	—	13,012	—	9,830	—	9,835	—	9,977	ps
3.3-V PCI	20 mA	—	–75	—	–97	—	–120	—	6,534	—	6,533	—	6,662	ps

Table 5–19. t_{XZ} IOE Microparameter Adders for Fast Slew Rate

Standard		MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTL	16 mA	—	0	—	0	—	0	—	0	—	0	—	0	ps
	8 mA	—	–56	—	–72	—	–89	—	–69	—	–69	—	–69	ps
3.3-V LVCMOS	8 mA	—	0	—	0	—	0	—	0	—	0	—	0	ps
	4 mA	—	–56	—	–72	—	–89	—	–69	—	–69	—	–69	ps
2.5-V LVTTL / LVCMOS	14 mA	—	–3	—	–4	—	–5	—	–7	—	–11	—	–11	ps
	7 mA	—	–47	—	–61	—	–75	—	–66	—	–70	—	–70	ps
1.8-V LVTTL / LVCMOS	6 mA	—	119	—	155	—	191	—	45	—	34	—	37	ps
	3 mA	—	207	—	269	—	331	—	34	—	22	—	25	ps
1.5-V LVCMOS	4 mA	—	606	—	788	—	970	—	166	—	154	—	155	ps
	2 mA	—	673	—	875	—	1,077	—	190	—	177	—	179	ps
3.3-V PCI	20 mA	—	71	—	93	—	114	—	–69	—	–69	—	–69	ps

Table 5–21. UFM Block Internal Timing Microparameters (Part 3 of 3)

Symbol	Parameter	MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t_{OE}	Delay from data register clock to data register output	180	—	180	—	180	—	180	—	180	—	180	—	ns
t_{RA}	Maximum read access time	—	65	—	65	—	65	—	65	—	65	—	65	ns
t_{OSCS}	Maximum delay between the OSC_ENA rising edge to the erase/program signal rising edge	250	—	250	—	250	—	250	—	250	—	250	—	ns
t_{OSCH}	Minimum delay allowed from the erase/program signal going low to OSC_ENA signal going low	250	—	250	—	250	—	250	—	250	—	250	—	ns

Figure 5–3 through Figure 5–5 show the read, program, and erase waveforms for UFM block timing parameters shown in Table 5–21.

Figure 5–3. UFM Read Waveforms

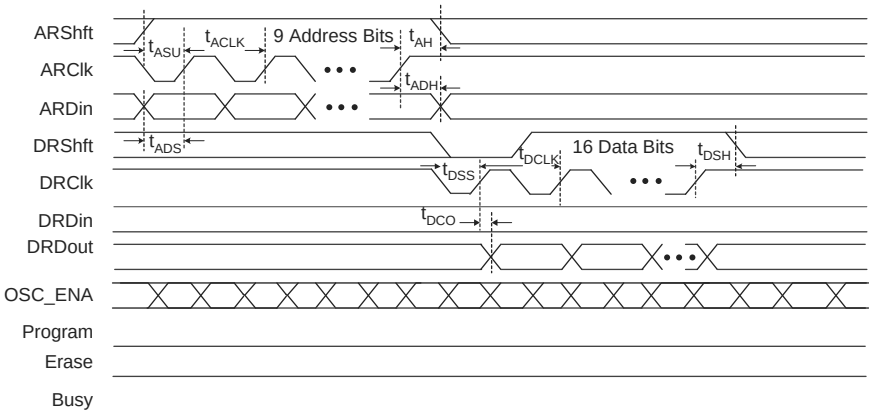


Table 5–29. External Timing Output Delay and t_{OD} Adders for Fast Slew Rate

I/O Standard		MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTL	16 mA	—	0	—	0	—	0	—	0	—	0	—	0	ps
	8 mA	—	65	—	84	—	104	—	–6	—	–2	—	–3	ps
3.3-V LVCMOS	8 mA	—	0	—	0	—	0	—	0	—	0	—	0	ps
	4 mA	—	65	—	84	—	104	—	–6	—	–2	—	–3	ps
2.5-V LVTTL / LVCMOS	14 mA	—	122	—	158	—	195	—	–63	—	–71	—	–88	ps
	7 mA	—	193	—	251	—	309	—	10	—	–1	—	1	ps
1.8-V LVTTL / LVCMOS	6 mA	—	568	—	738	—	909	—	128	—	118	—	118	ps
	3 mA	—	654	—	850	—	1,046	—	352	—	327	—	332	ps
1.5-V LVCMOS	4 mA	—	1,059	—	1,376	—	1,694	—	421	—	400	—	400	ps
	2 mA	—	1,167	—	1,517	—	1,867	—	757	—	743	—	743	ps
3.3-V PCI	20 mA	—	3	—	4	—	5	—	–6	—	–2	—	–3	ps

Table 5–30. External Timing Output Delay and t_{OD} Adders for Slow Slew Rate

I/O Standard		MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTL	16 mA	—	7,064	—	6,745	—	6,426	—	5,966	—	5,992	—	6,118	ps
	8 mA	—	7,946	—	7,627	—	7,308	—	6,541	—	6,570	—	6,720	ps
3.3-V LVCMOS	8 mA	—	7,064	—	6,745	—	6,426	—	5,966	—	5,992	—	6,118	ps
	4 mA	—	7,946	—	7,627	—	7,308	—	6,541	—	6,570	—	6,720	ps
2.5-V LVTTL / LVCMOS	14 mA	—	10,434	—	10,115	—	9,796	—	9,141	—	9,154	—	9,297	ps
	7 mA	—	11,548	—	11,229	—	10,910	—	9,861	—	9,874	—	10,037	ps
1.8-V LVTTL / LVCMOS	6 mA	—	22,927	—	22,608	—	22,289	—	21,811	—	21,854	—	21,857	ps
	3 mA	—	24,731	—	24,412	—	24,093	—	23,081	—	23,034	—	23,107	ps
1.5-V LVCMOS	4 mA	—	38,723	—	38,404	—	38,085	—	39,121	—	39,124	—	39,124	ps
	2 mA	—	41,330	—	41,011	—	40,692	—	40,631	—	40,634	—	40,634	ps
3.3-V PCI	20 mA	—	261	—	339	—	418	—	6,644	—	6,627	—	6,914	ps

Table 5–33. MAX II Maximum Output Clock Rate for I/O

I/O Standard		MAX II / MAX IIG			MAX IIZ		
		–3 Speed Grade	–4 Speed Grade	–5 Speed Grade	–6 Speed Grade	–7 Speed Grade	–8 Speed Grade
3.3-V LVTTL	304	304	304	304	304	304	MHz
3.3-V LVCMOS	304	304	304	304	304	304	MHz
2.5-V LVTTL	220	220	220	220	220	220	MHz
2.5-V LVCMOS	220	220	220	220	220	220	MHz
1.8-V LVTTL	200	200	200	200	200	200	MHz
1.8-V LVCMOS	200	200	200	200	200	200	MHz
1.5-V LVCMOS	150	150	150	150	150	150	MHz
3.3-V PCI	304	304	304	304	304	304	MHz

JTAG Timing Specifications

Figure 5–6 shows the timing waveforms for the JTAG signals.

Figure 5–6. MAX II JTAG Timing Waveforms

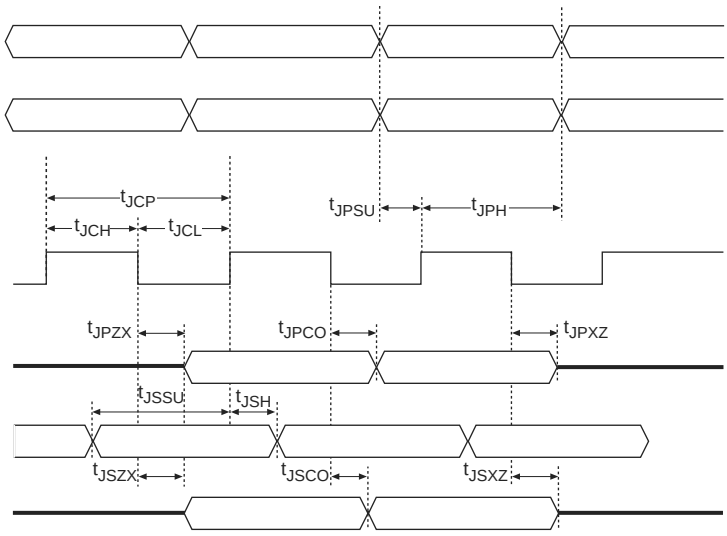


Table 5–34 shows the JTAG Timing parameters and values for MAX II devices.

Table 5–34. MAX II JTAG Timing Parameters (Part 1 of 2)

Symbol	Parameter	Min	Max	Unit
t_{JCP} *(1)*	TCK clock period for V_{CCIO1} = 3.3 V	55.5	—	ns
	TCK clock period for V_{CCIO1} = 2.5 V	62.5	—	ns
	TCK clock period for V_{CCIO1} = 1.8 V	100	—	ns
	TCK clock period for V_{CCIO1} = 1.5 V	143	—	ns
t_{JCH}	TCK clock high time	20	—	ns
t_{JCL}	TCK clock low time	20	—	ns